## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	(substrate and wiring and conductive and cap and destructive and interference and graded and index and refraction and photoresist and etching and gap and dielectric and high and chemical and deposition).clm.	US-PGPUB	OR	ON	2008/12/12
L2	0	substrate and wiring and conductive and cap and destructive and interference and graded and index and refraction and photoresist and etching and gap and dielectric and high and chemical and chemical and chemical and cheposition	ippris, epc); JPO; deriwent	OR	ON	(2008/12/12 13:28

	chemical and vapor and deposition and constant).clm.				
L4 O	substrate and silicon and surface and titanium and wiring and protective and cap and destructive and interference and graded and index and refraction and photoresist and etching and ap and dielectric and high and chemical and vapor and deposition and constant	FPRS; EPO; JPO; DIERWENT	OR .	ON	2008/12/12

L5	О	(substrate and wiring and cap and plasma and destructive and interference and graded and index and refraction and photoresist and etching and gap and dielectric and high and density and plasma and chemical and vapor and deposition and constant and aspect and ratio and planarized). clm.	US-PGPUB	OR	ON	2008/12/12 13:35
L6	O	substrate and wiring and antireflective and cap and plasma and destructive and interference and graded and index and refraction and photoresist and etching and gap and dielectric and high and density and plasma and chemical and vapor and deposition and constant and aspect and ratio and planarized	FPRS; EPO; JPO; DERWENT	OR	ON	2008/12/12

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